

BFR30LT1, BFR31LT1

JFET Amplifiers

N-Channel

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	25	Vdc
Gate – Source Voltage	V_{GS}	25	Vdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

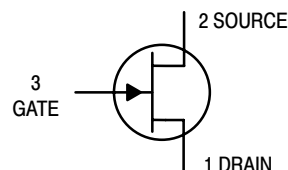
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- Device mounted on FR4 glass epoxy printed circuit board using the recommended footprint.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

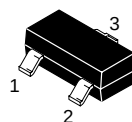


ON Semiconductor®

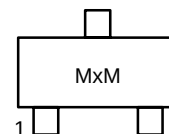
<http://onsemi.com>



MARKING DIAGRAM



SOT-23
CASE 318
STYLE 10



x = 1 or 2
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BFR30LT1	SOT-23	3000/Tape & Reel
BFR30LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BFR31LT1	SOT-23	3000/Tape & Reel
BFR31LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BFR30LT1, BFR31LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Gate Reverse Current ($V_{GS} = 10\text{ Vdc}, V_{DS} = 0$)	I_{GSS}	–	0.2	nAdc
Gate Source Cutoff Voltage ($I_D = 0.5\text{ nAdc}, V_{DS} = 10\text{ Vdc}$)	$V_{GS(OFF)}$	–	5.0	Vdc
Gate Source Voltage ($I_D = 1.0\text{ mAdc}, V_{DS} = 10\text{ Vdc}$)	V_{GS}	–0.7	–3.0	Vdc
		–	–1.3	
($I_D = 50\text{ }\mu\text{Adc}, V_{DS} = 10\text{ Vdc}$)		–	–4.0	
		–	–2.0	

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current ($V_{DS} = 10\text{ Vdc}, V_{GS} = 0$)	I_{DSS}	4.0	10	mAdc
		1.0	5.0	

SMALL-SIGNAL CHARACTERISTICS

Forward Transconductance ($I_D = 1.0\text{ mAdc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	$ y_{fs} $	1.0	4.0	mmhos
		1.5	4.5	
($I_D = 200\text{ }\mu\text{Adc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)		0.5	–	
		0.75	–	
Output Admittance ($I_D = 1.0\text{ mAdc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	$ y_{os} $	40	25	μmhos
($I_D = 200\text{ }\mu\text{Adc}, V_{DS} = 10\text{ Vdc}$)		20	15	
Input Capacitance ($I_D = 1.0\text{ mAdc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ MHz}$)	C_{iss}	–	5.0	pF
($I_D = 200\text{ }\mu\text{Adc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ MHz}$)		–	4.0	
Reverse Transfer Capacitance ($I_D = 1.0\text{ mAdc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ MHz}$)	C_{rss}	–	1.5	pF
($I_D = 200\text{ }\mu\text{Adc}, V_{DS} = 10\text{ Vdc}, f = 1.0\text{ MHz}$)		–	1.5	

TYPICAL CHARACTERISTICS

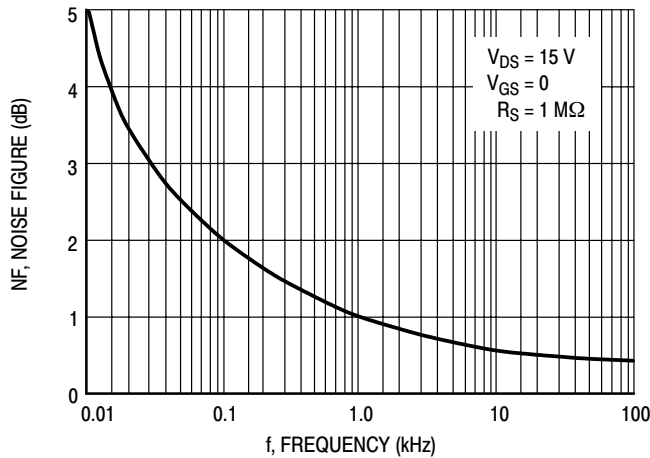


Figure 1. Noise Figure versus Frequency

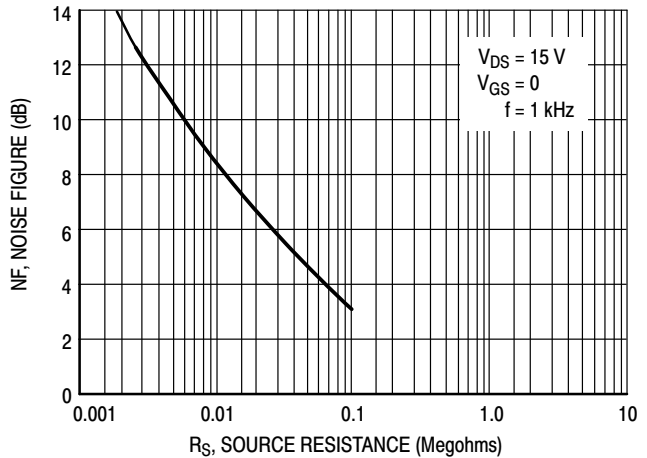


Figure 2. Noise Figure versus Source Resistance

TYPICAL CHARACTERISTICS

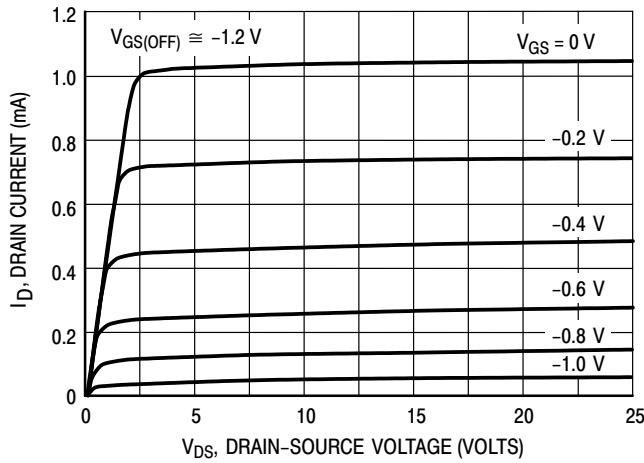


Figure 3. Typical Drain Characteristics

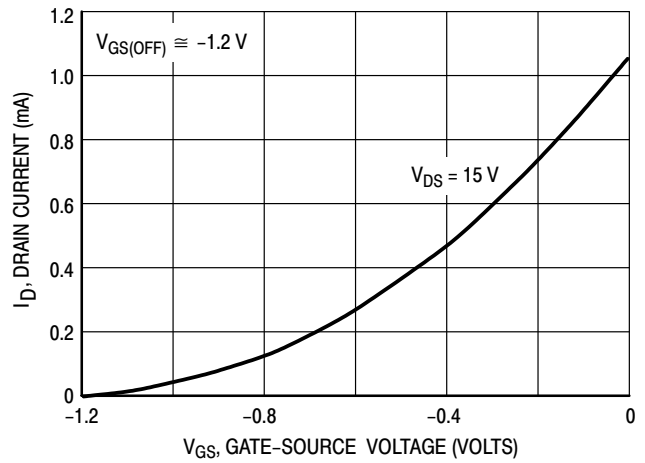


Figure 4. Common Source Transfer Characteristics

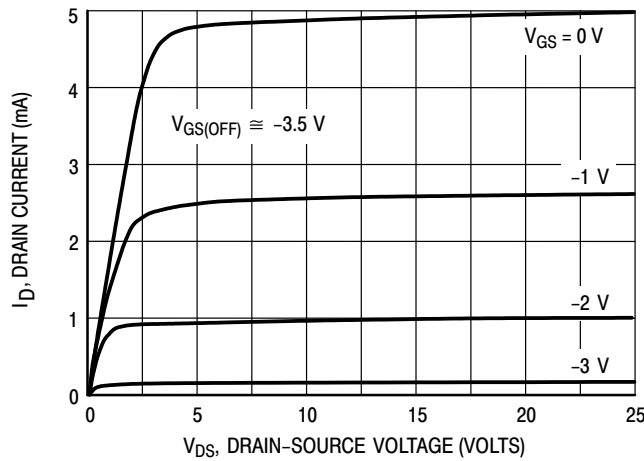


Figure 5. Typical Drain Characteristics

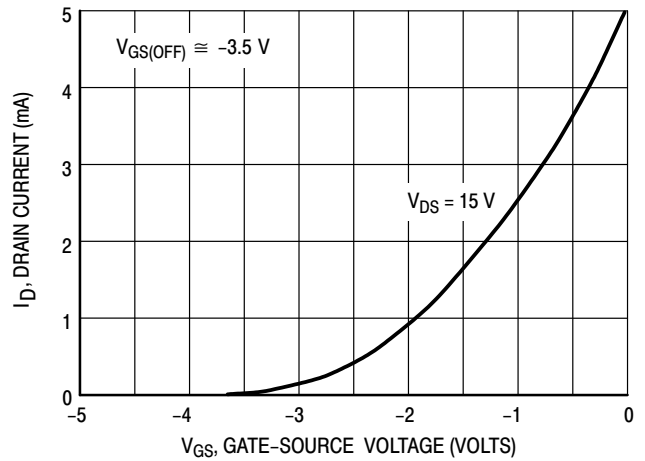


Figure 6. Common Source Transfer Characteristics

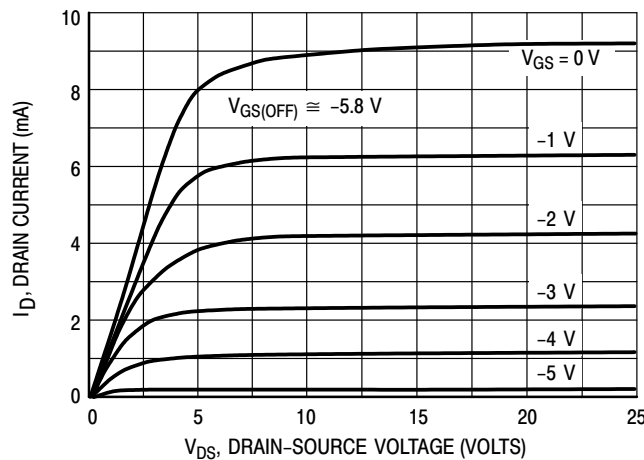


Figure 7. Typical Drain Characteristics

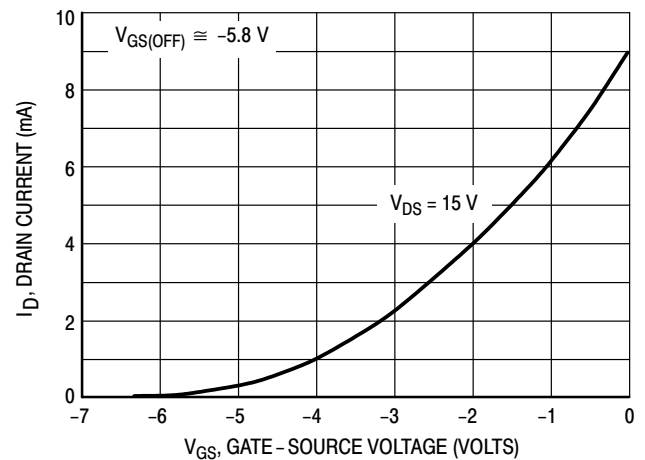
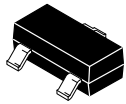


Figure 8. Common Source Transfer Characteristics

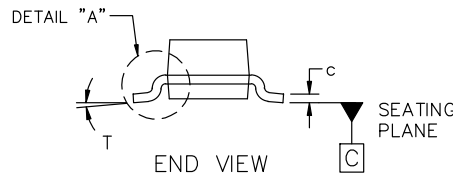
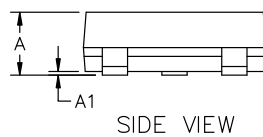
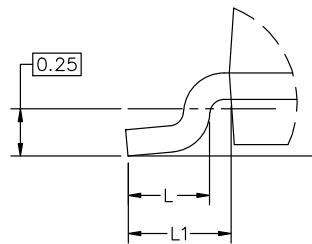
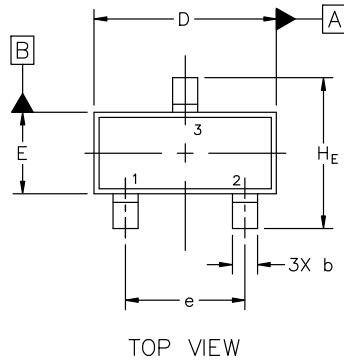
Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS} .



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

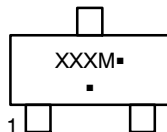


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

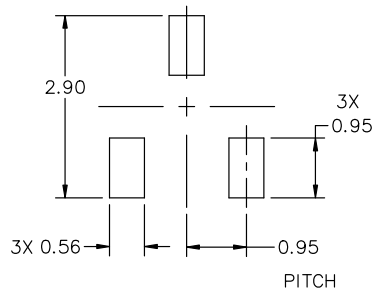
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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